

EVVOSEMI[®]

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

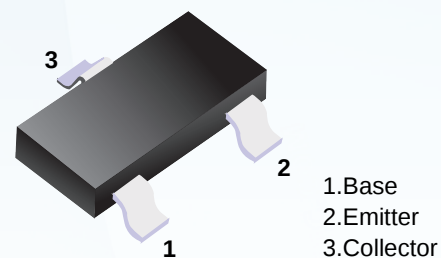
Product Specification

▶ Domestic	Part Number	EV2SA1298-X-S1
▶ Overseas	Part Number	2SA1298-X
▶ Equivalent	Part Number	2SA1298-X

"S1" means SOT-23

EV is the abbreviation of name EVVO

PNP Transistors



■ Simplified outline(SOT-23)

■ Features

- Collector Current Capability $I_C = -0.8A$
- Collector Emitter Voltage $V_{CE0} = -30V$
- Low Frequency Power Amplifier Application
- Power Switching Applications
- Complementary to 2SC3265

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-35	V
Collector - Emitter Voltage	V_{CEO}	-30	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-800	mA
Collector Power Dissipation	P_C	200	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	625	$^\circ C/W$
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature range	T_{stg}	-55 to 150	

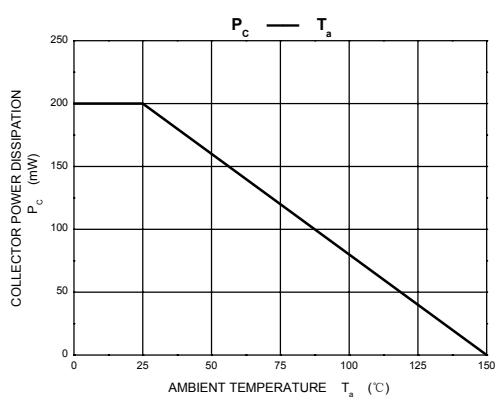
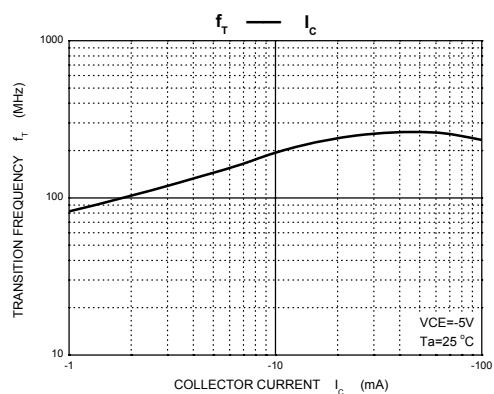
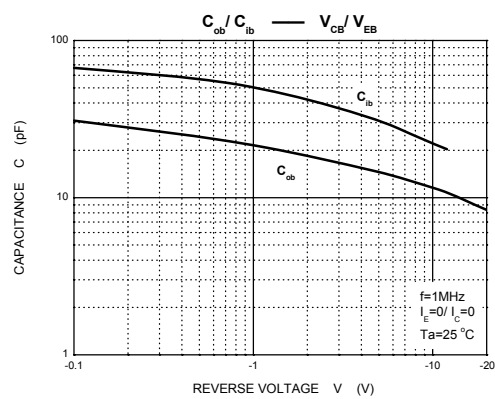
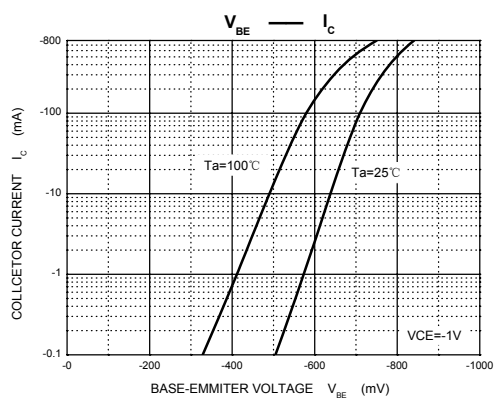
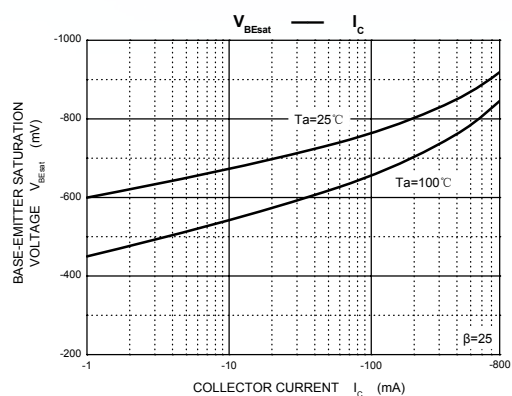
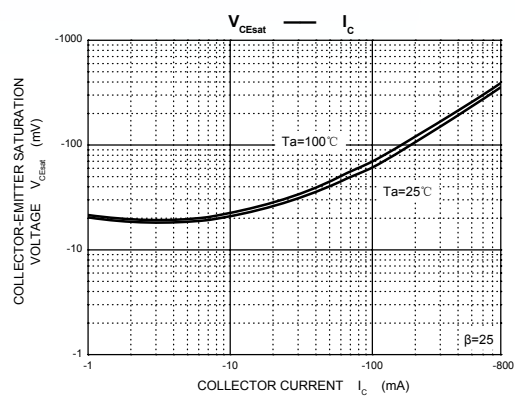
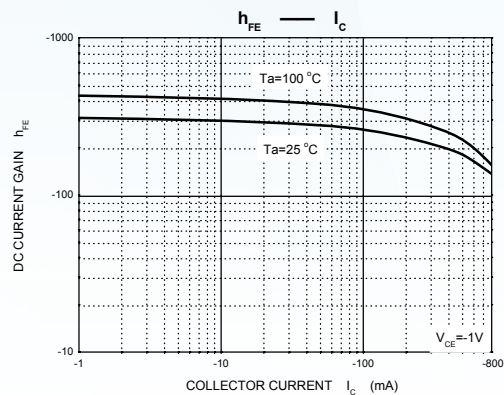
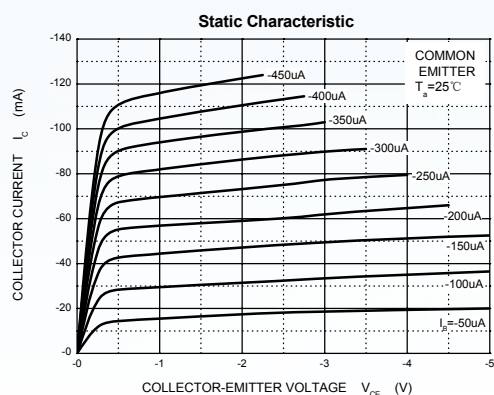
■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = -1mA, I_E = 0$	-35			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = -10mA, I_B = 0$	-30			
Emitter - base breakdown voltage	V_{EBO}	$I_E = -1mA, I_C = 0$	-5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -30V, I_E = 0$			-0.1	uA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -20mA$			-0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500mA, I_B = -20mA$			-1.2	
Base - emitter voltage	V_{BE}	$V_{CE} = -1V, I_C = -10mA$			-0.8	
DC current gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -100mA$	100		320	
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -800mA$	40			
Collector output capacitance	C_{ob}	$V_{CB} = -6V, I_E = 0, f = 1MHz$		13		pF
Transition frequency	f_T	$V_{CE} = -5V, I_C = -10mA$		120		MHz

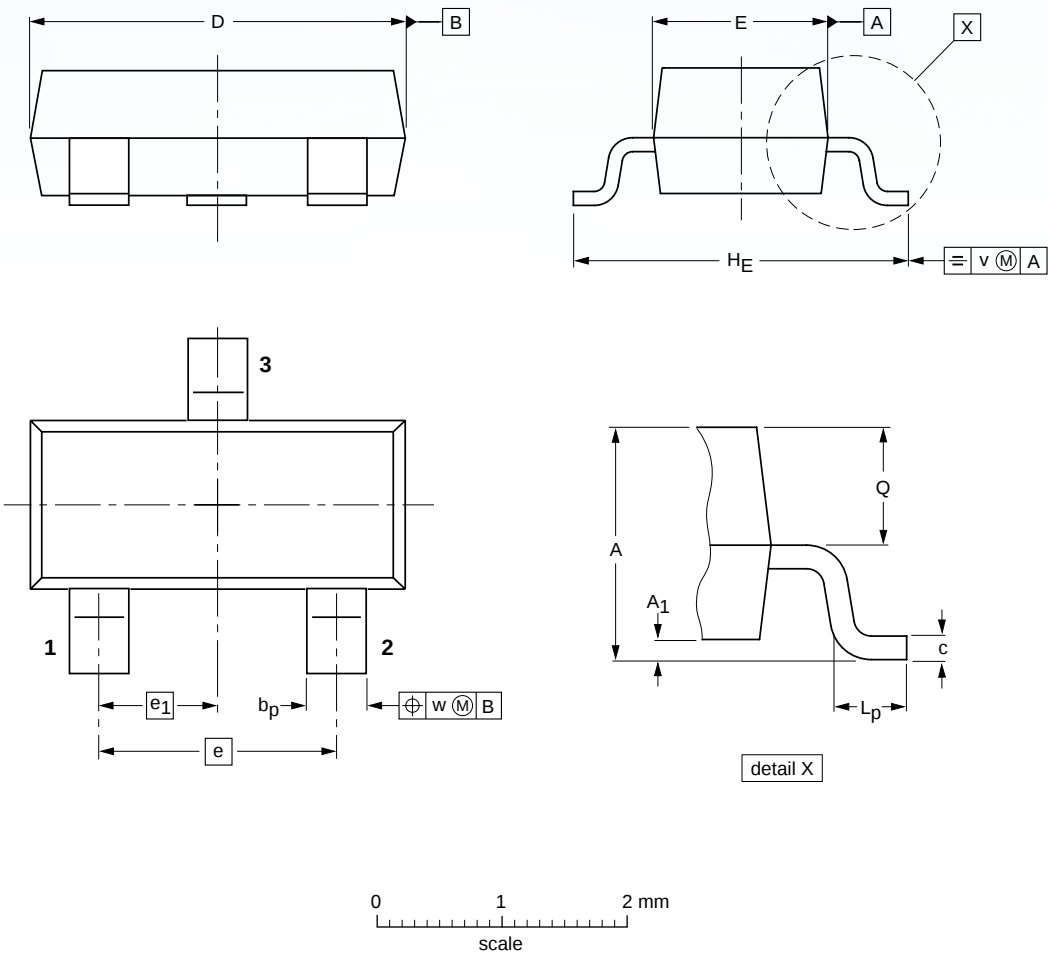
■ Classification of $h_{FE(1)}$

Type	EV2SA1298-O-S1	EV2SA1298-Y-S1
Range	100-200	160-320
Marking	IO	IY

■ Typical Characteristics



■ SOT-23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

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